



New Product

Si1410EDH
Vishay Siliconix

N-Channel 20-V (D-S) MOSFET

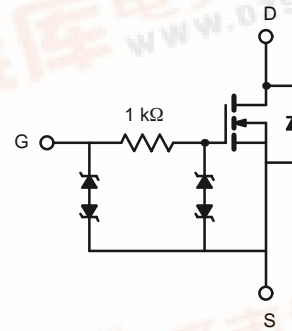
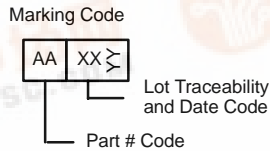
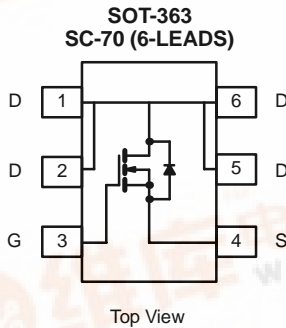
PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
20	0.070 @ $V_{GS} = 4.5$ V	3.7
	0.080 @ $V_{GS} = 2.5$ V	3.4
	0.100 @ $V_{GS} = 1.8$ V	3.0

FEATURES

- TrenchFET® Power MOSFETS: 1.8-V Rated
- ESD Protected: 2000 V
- Thermally Enhanced SC-70 Package

APPLICATIONS

- Load Switching
- PA Switch
- Level Switch



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)					
Parameter	Symbol	5 secs	Steady State	Unit	
Drain-Source Voltage	V_{DS}	20		V	
Gate-Source Voltage	V_{GS}	± 12			
Continuous Drain Current ($T_J = 150^\circ\text{C}$) ^a	I_D	$T_A = 25^\circ\text{C}$	3.7	2.9	A
		$T_A = 85^\circ\text{C}$	2.6	2.0	
Pulsed Drain Current	I_{DM}	8			
Continuous Diode Current (Diode Conduction) ^a	I_S	1.4	0.9		
Maximum Power Dissipation ^a	P_D	$T_A = 25^\circ\text{C}$	1.56	1.0	W
		$T_A = 85^\circ\text{C}$	0.81	0.52	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 150		$^\circ\text{C}$	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	$t \leq 5$ sec	R_{thJA}	60	80	$^\circ\text{C/W}$
	Steady State		100	125	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	34	45	

Notes:
a. Surface Mounted on 1" x 1" FR4 Board.

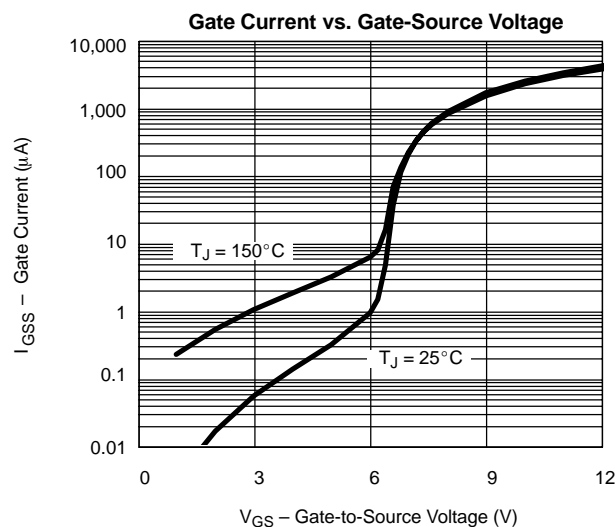
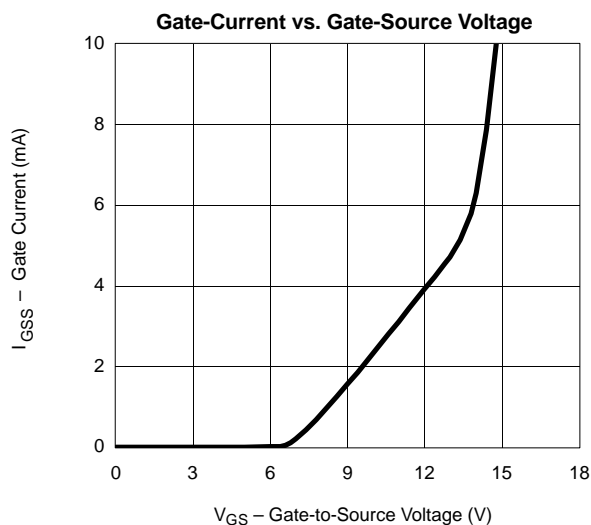


SPECIFICATIONS (T _J = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	0.45			V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±4.5 V			±1	μA
		V _{DS} = 0 V, V _{GS} = ±12 V			±10	mA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 16 V, V _{GS} = 0 V			1	μA
		V _{DS} = 16 V, V _{GS} = 0 V, T _J = 85 °C			5	
On-State Drain Current ^a	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 4.5 V	4			A
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = 4.5 V, I _D = 3.7 A		0.055	0.070	Ω
		V _{GS} = 2.5 V, I _D = 3.4 A		0.065	0.080	
		V _{GS} = 1.8 V, I _D = 1.7 A		0.080	0.100	
Forward Transconductance ^a	g _{fs}	V _{DS} = 10 V, I _D = 3.7 A		10		S
Diode Forward Voltage ^a	V _{SD}	I _S = 1.4 A, V _{GS} = 0 V		0.75	1.1	V
Dynamic^b						
Total Gate Charge	Q _g	V _{DS} = 10 V, V _{GS} = 4.5 V, I _D = 3.7 A		5.6	8	nC
Gate-Source Charge	Q _{gs}			0.75		
Gate-Drain Charge	Q _{gd}			1.10		
Turn-On Delay Time	t _{d(on)}	V _{DD} = 10 V, R _L = 10 Ω I _D ≅ 1 A, V _{GEN} = 4.5 V, R _G = 6 Ω		0.15	0.25	μs
Rise Time	t _r			0.4	0.6	
Turn-Off Delay Time	t _{d(off)}			1.9	2.8	
Fall Time	t _f			1.2	1.8	

Notes

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- b. Guaranteed by design, not subject to production testing.

TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)

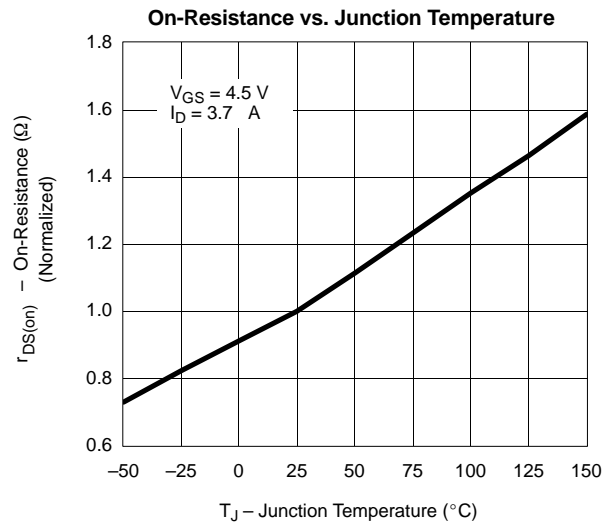
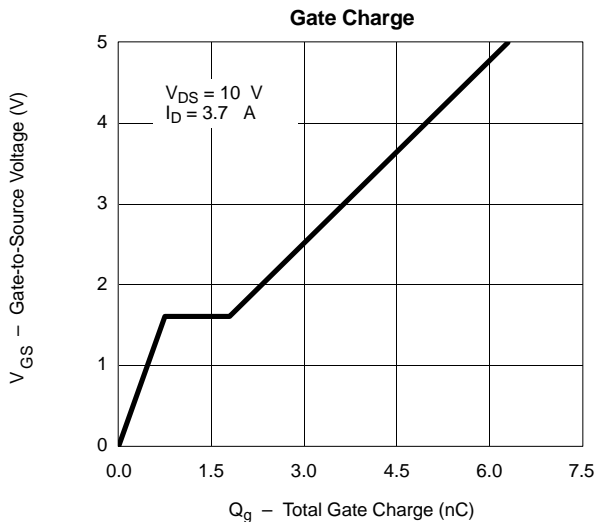
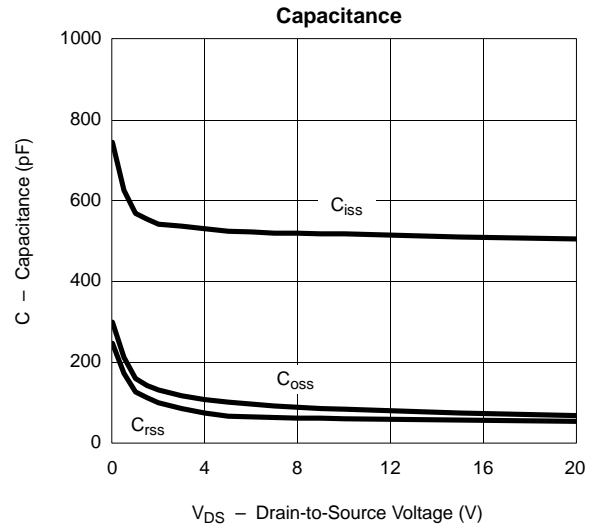
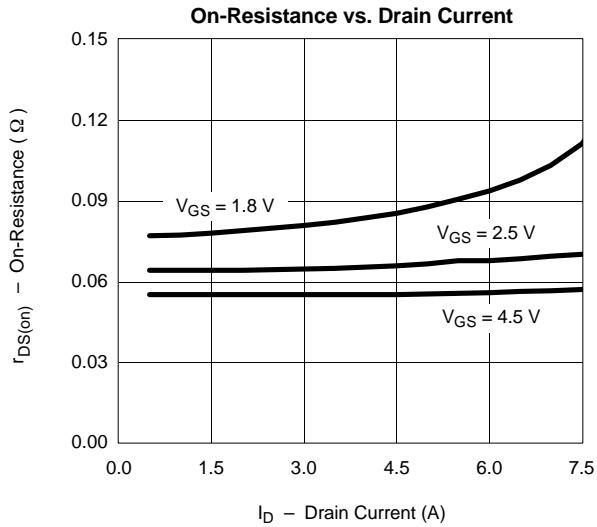
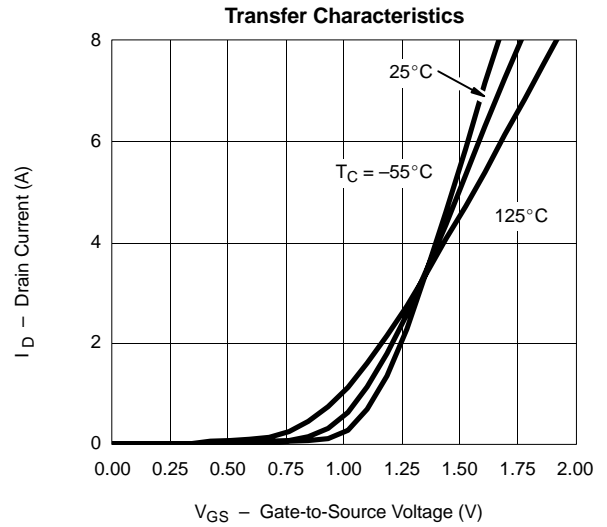
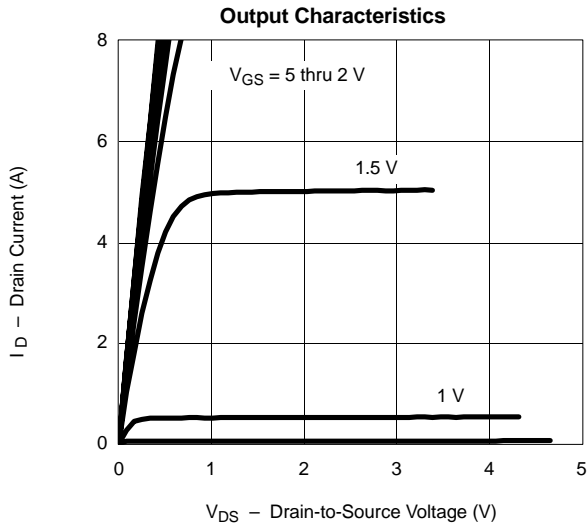




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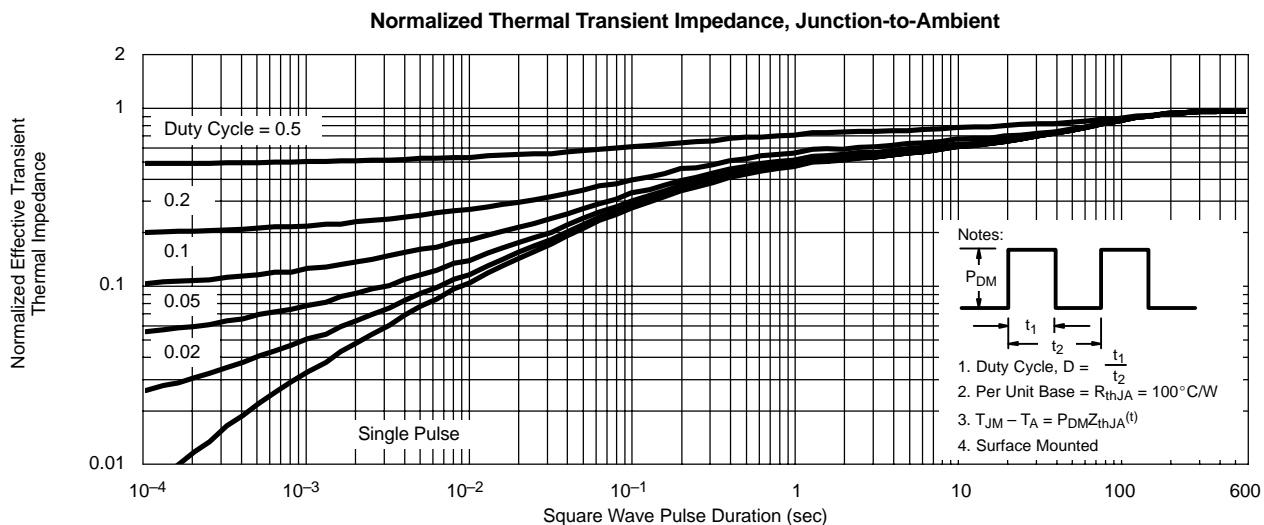
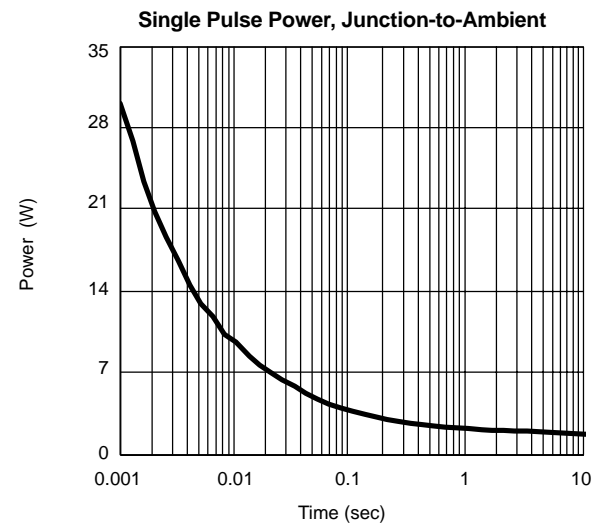
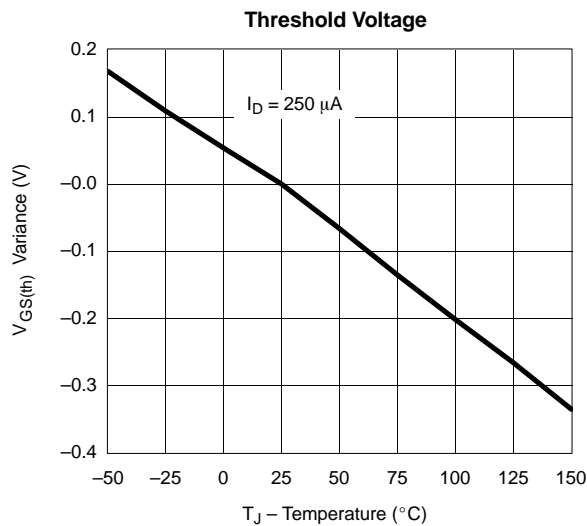
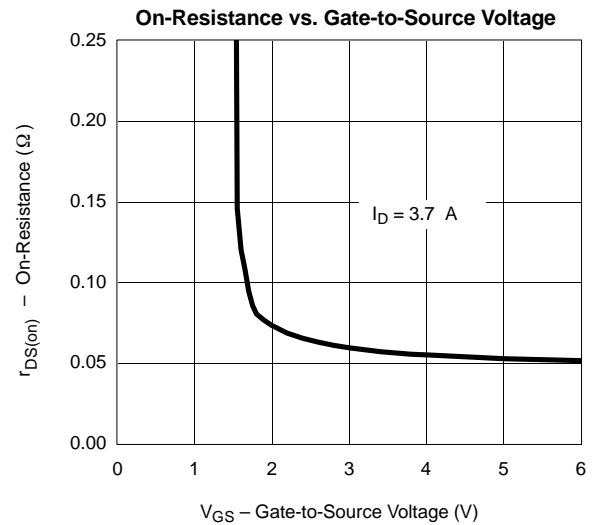
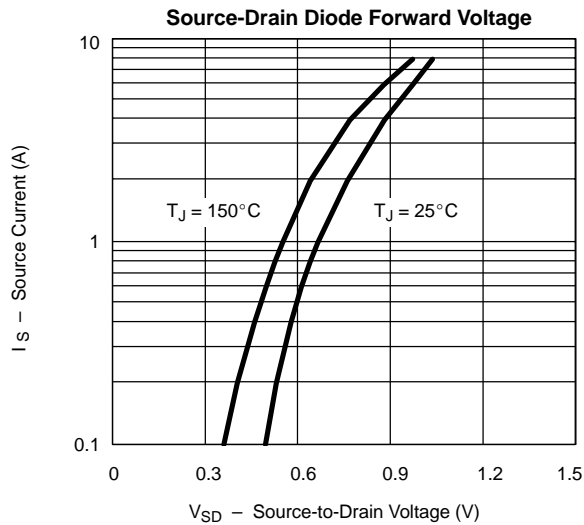
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